Program

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors III

An ECI Conference Series

June 26 - July 1, 2011 Hong Kong, China

Conference Chair

Yue Kuo Texas A&M University, USA

Conference Co-Chair

Gennadi Bersuker SEMATECH, USA



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Sunday, June 26, 2011

16:30 – 18:30	Registration
18:30 – 20:00	Welcome Reception

<u>Notes</u>

- Welcome Reception: Salon II & III
- Technical Session: Regency Ballroom I
- Poster Session with Social Hour: Salon I
- Meals:

0	June 27	Lunch & Dinner	Regency Ballroom I
0	June 28	Lunch & Dinner	Regency Ballroom I
0	June29	Lunch	Regency Ballroom I
		Dinner on your own	
0	June 30	Reception	Sha Tin 18 Upper Deck
		Banquet Dinner	Sha Tin 18 Lower Deck
0	July 1	Lunch	Regency Ballroom I

- Audiotaping, videotaping and photography of presentations are prohibited.
- Speakers Please leave at least 3-5 minutes for questions and discussion.
- Please do not smoke at any conference functions.
- Turn your cellular telephones to vibrate or off during technical sessions.
- Be sure to make any corrections to your name/contact information on the Master Participant List or confirm (with your initials) that the listing is correct. A corrected copy will be sent to all participants after the conference.

<u>Monday, June 27, 2011</u>	
07:00 - 08:00	Breakfast Buffet
08:00 – 08:10	Welcome and Conference Overview Y. Kuo and G. Bersuker, Conference Chairs
	<u>Plenary Talks</u> Session Chair: Y. Kuo, Texas A&M University
08:10 – 08:55	It's a 3D World - Challenges and opportunities for 3D logic and memory ULSI devices R. Jammy, SEMATECH
08:55 – 09:40	Semiconductor technology evolution for ULSIC HK. Kang, Samsung Electronics
09:40 – 10:25	Nanoscale metal silicides L. J. Chen, National Tsing Hua University
10:25 – 10:50	Coffee Break
	Nano Devices Session Chairs: G. Bersuker, SEMATECH T. Asano, Kyushu University
10:50 – 11:20	Silicon grow-in-place nanowires and their applications S. Fonash, Pennsylvania State University
11:20 – 11:50	In-plane silicon nanowires for field effect transistor applications L. Yu and P. R. i Cabarrocas, CNRS
11:50 – 12:20	Application of graphene and carbon nanotubes to transistors and interconnects S. Sato, M. Nihei, and N. Yokoyama, AIST
12:20 – 14:00	Lunch
14:00 -	Afternoon Coffee
14:00 – 15:30	Panel Discussion: Challenges in extremely large and small scalings Moderators: S. Srinivasan and HK. Kang
16:00 – 18:30	Free time for discussion, ad hoc sessions, leisure
18:30 – 19:30	Poster Session/Social Hour Session Chairs: F. Yan, Hong Kong Polytechnic University
19:30 – 20:30	Dinner
20:30 – 21:30	Social Hour & Discussion

Tuesday, June 28, 2011

07:00 – 08:20	Breakfast Buffet
	IC Devices & Materials Session Chairs: W. Milne, Cambridge University S. J. Fonash, Pennsylvania State University
08:20 – 09:00	Keynote: Unipolar CMOS logic for post-Si ULSI and for TFT technologies T. P. Ma, Yale University
09:00 – 09:30	Epitaxial techniques for semiconductor manufacturing S. Srinivasan, Applied Materials
09:30 – 10:00	Electron and hole trapping in polycrystalline and amorphous oxides for novel CMOS devices A. Shluger, K. McKenna, University College London; G. Bersuker, SEMATECH
10:00 – 10:30	Coffee Break
	<u>Oxide and Organic TFTs</u> Session Chairs: J. Murota, Tohoku University S. Srivanasan, Applied Materials
10:30 – 11:00	Zinc Oxide-Based Transparent TFTs Produced at Low Temperature W. Milne, F. Li, M. Mann, R. Waddingham, A. Kiani and A. Flewitt, Cambridge University
11:00 – 11:30	High performance a-IGZO TFT and TFT circuits for display application J. Jang, Kyung Hee University
11:30 – 11:50	Comparative analysis of organic thin film transistor structures for flexible E- paper and AMOLED displays L. Feng, X. Xu, X. Guo, Shanghai Jiao Tong University
12:00 – 14:00	Lunch
14:00 —	Afternoon Coffee
14:00 – 16:00	Panel Discussion: Challenges in materials and fabrication Moderators: M. Caymax and J. Jang
16:30 – 19:00	Free Time for discussion, ad hoc sessions, leisure.
19:00 – 20:30	Dinner
20:30 – 21:30	Social Hour & Discussion

Wednesday, June 29, 2011

07:00 - 08:00	Breakfast Buffet
	<u>Memories and Interfaces</u> Session Chairs: G. Fortunato, CNR-IMM S. Sato, AIST
08:00 – 08:30	Structural characteristics of transition metal oxides enabling resistive memory operations G. Bersuker, SEMATECH
08:30 - 09:00	Nonvolatile memories for nano and giga electronics applications Y. Kuo, Texas A&M University
09:00 – 09:30	Understanding the switching mechanism in RRAM devices and the dielectric breakdown of ultrathin high-k gate stacks from first principles calculations B. Magyari-Kope and Y. Nishi, Stanford University
09:30 – 9:50	Manipulation of graphene properties by interface engineering J. B. Xu, X. M. Wang, C. L. Wang, W. G. Xie, and J. Du, The Chinese University of Hong Kong
10:00 – 10:30	Coffee Break
	<u>Si-based TFTs</u> Session Chairs: T. P. Ma, Yale University Y. Saito, Toshiba
10:30 – 11:00	Short channel effects and drain field relief architectures in polysilicon TFTs G. Fortunato, M. Cuscunà, L. Maiolo, L. Mariucci, M. Rapisarda, A. Pecora and A. Valletta, CNR-IMM, S.D. Brotherton, TFT Consultant, UK
11:00 – 11:30	The potential application of oxide thin film transistor for active matrix display T. Mohammed-Brahim and K. Kandoussi, University Rennes 1
11:30 – 12:00	Single-grain germanium TFTs R. Ishihara, T. Chen, Delft University of Technology
12:00 – 12:20	Source-gated transistors for versatile large area electronic circuit design and fabrication R. A. Sporea, C. Opoku, M. Shkunov, J. M. Shannon, and S. Ravi P. Silva, Advanced Technology Institute; X. Guo, Shanghai Jiao Tong University
12:20 – 14:00	Lunch
14:00	Free Time for leisure, recreation, discussion <i>ad hoc</i> sessions Optional Excursions Dinner on your own

Thursday, June 30, 2011

07:00 - 08:00	Breakfast
	IC beyond Si Session Chairs: O. Bonnaud, University Rennes 1 H. S. Kwok, Hong Kong University of Science Technology
08:30 – 09:00	SiGe, Ge and III-V materials and processes for beyond-Si CMOS and more- than-Moore applications M. Caymax, IMEC
09:00 – 09:30	Electrical atomically controlled CVD processing for doping in future Si-based devices J. Murota and M. Sakuraba, Tohoku University; B. Tillack, IHP and Technical University of Berlin
09:30 – 10:00	Physical modeling of charge transport and degradation in high-K stacks for logic device and memory applications L. Larcher, A. Padovani, and L. Vandelli, Università di Modena e Reggio Emilia; G. Bersuker, SEMATECH
10:00 – 10:30	Coffee Break
	TFT Devices and ProcessesSession Chairs:C. Matty, IMECL. Larcher, Università di Modena e Reggio
10:30 – 11:00	Success in measuring the lowest off-state current of transistors in the world Y. Sekine, K. Furutani, Y. Shionoiri, K. Kato, J. Koyama, S. Yamazaki, Semiconductor Energy Laboratory
11:00 – 11:30	Self-heating Issue of poly-Si TFT on glass substrate T. Asano and G. Nakagawa, Kyushu University
11:30 – 12:00	Bridged-grain TFT H. S. Kwok, M Wong, S Y Zhao and W Zhou, Hong Kong University of Science and Technology
12:20 – 14:00	Lunch
14:00 -	Afternoon Coffee
14:00 – 16:00	Panel Discussion: Challenges in Applications Moderators: G. Bersuker and Y. Saito
16:30 – 19:00	Free Time for leisure, recreation, discussion ad hoc sessions
19:00 – 22:00	Conference Banquet

Friday, July 1, 2011

07:00 – 08:00	Breakfast Buffet
	Packages and New Device PrinciplesSession Chairs:J. Jang, Kyung Hee UniversityA. Shluger, University College London
08:00 – 08:40	Keynote: Recent advances on nano-materials for advanced packaging applications C. P. Wong, Chinese University of Hong Kong and Georgia Institute of Technology
08:40 – 09:10	Spin-based MOSFET and its applications Y. Saito, T. Inokuchi, M. Ishikawa, H.i Sugiyama, T. Marukame, and T. Tanamoto, Toshiba Corporation
09:10 – 09:40	Flexible thin film transistor arrays as an enabling platform technology: Opportunities and challenges G. B. Raupp, City University of Hong Kong
09:40 – 10:10	Coffee Break
10:10 – 11:50	TFT New ApplicationSession Chairs:C. P. Wong, Chinese University of Hong Kong R. Ishihara, Delft University of Technology
10:10 – 10:40	Vertical channel thin film transistor: Improvement approach similar to multigate monolithic CMOS technology O. Bonnaud, Z. Peng , E. Jacques and R. Rogel, University Rennes 1
10:40 – 11:00	Low power 6.0-Inch extended graphics array reflective liquid crystal display using crystalline indium gallium zinc oxide semiconductor with electronic paper function M. Kaneyasu, H. Miyake, T. Nishi, Y. Hirakata, J. Koyama, S. Yamazaki Semiconductor Energy Laboratory Co.; R. Sato, M. Sakakura, Advanced Film Device Inc.
11:00– 11:30	Biosensors based on organic thin film transistors F. Yan, Hong Kong Polytechnic University
11:30 – 11:50	MILC PMOS poly-silicon TFT circuits and application in SOP P. Sun, S. Zhao, TK. Ho, M. Wong, and H. S. Kwok, Hong Kong University of Science and Technology; Z. Meng, Nankai University
11:50 - 12:00	Conclusion of Conference: Wrap-up, Thanks, and Future Y. Kuo, Texas A&M University, and G. Bersuker, SEMATECH
12:10	Lunch
14:00	Departure

List of Posters

Authors	S	Торіс
1.	S. Amano, H. Miyake, T. Nishi, Y. Hirakata, J. Koyama, S. Yamazaki (SEL)	Low power 6.0-inch extended graphics array transmissive liquid crystal display using crystalline indium gallium zinc oxide semiconductor with variable frame frequency
2.	Y. Yuan, E. Ivanov (Tosoh)	Formation and characterization of rare earth metal silicides
3.	J. Li, F. Yan (Hong Kong Polytechnic University)	Low voltage organic field-effect transistors based on poly(2,5bis(3-alkythiophen-2-yl)-thieno[3,2-b]thiophene) semiconducting polymer
4.	Sun Z., J. Li, F. Yan (Hong Kong Polytechnic University)	High carrier mobility of P3HT induced by TiO ₂ nanorods